MB200DU12FJ

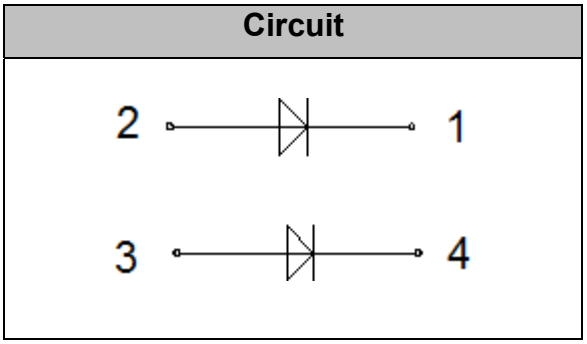
1200V SiC Power Module
Dual Diode Pack

V_{DC}	1200V
I_F	2×100A
$T_{J,max}$	175°C

Applications

- Welding equipment
- Uninterruptible power supply (UPS)
- High frequency power supply
- Induction heating
- High speed rectifiers

Circuit



Features

- SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on V_F
- Very low stray inductance
- Low forward voltage
- Isolated package (SOT-227)
- Low noise switching
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Absolute Maximum Ratings (T_J=25°C unless otherwise specified, per leg)

Parameter	Symbol	Test Conditions	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	T_J=25°C	1200	V
DC Blocking Voltage	V_{DC}	T_J=25°C	1200	V
Continuous Forward Current	I_F	T_C=25°C, T_J=175°C	152	A
		T_C=99°C, T_J=175°C	100	
		T_C=135°C, T_J=175°C	66	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	T_C=25°C, T_P=10ms, Half Sine Wave	625	A
I^2t Value	$\int I^2dt$	T_C=25°C, T_P=10ms	1953	A^2s
Power Dissipation	P_{Tot}	T_C=25°C	453	W
Junction Temperature	T_J		-55…175	°C
Storage Temperature	T_{STG}		-40…125	°C

Electrical Characteristics (T_J=25°C unless otherwise specified, per leg)

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Reverse Current	I_R	V_R=1200V, T_J=25°C	--	0.6	100	μA
		V_R=1200V, T_J=175°C	--	8.6	--	
Forward Voltage	V_F	I_F=100A, T_J=25°C	--	1.5	1.7	V
		I_F=100A, T_J=175°C	--	2.3	--	
Total Capacitance	C	V_R=0V, f=1MHz	--	6480	--	pF
		V_R=400V, f=1MHz	--	450	--	
		V_R=800V, f=1MHz	--	354	--	
Total Capacitive Charge	Q_C	V_R=800V	--	481	--	nC
Capacitance Stored Energy	E_C	V_R=800V	--	124	--	μJ

Thermal and Package Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Value	Unit
Thermal Resistance, Junction to Case	R_{thJC}	Per leg	0.33	°C/W
Isolation Breakdown Voltage	V_{isol}	AC, 50Hz (R.M.S), T=3s	3600	V
Mounting Torque	M	Recommended (M4 screw)	1~1.5	Nm
Terminal Connection Torque		Recommended (M4 screw)	1~1.5	
Weight	W		32	g

Typical Performance Per Leg

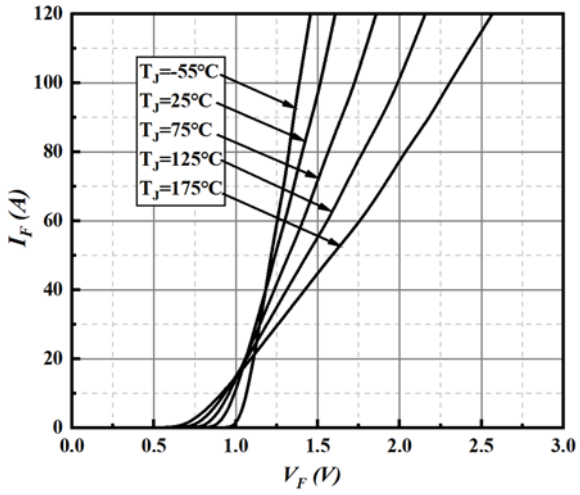


Fig1. Forward Characteristics (parameterized on T_J)

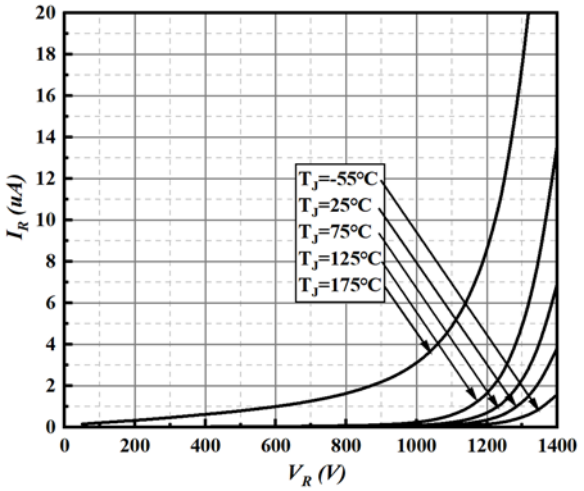


Fig2. Reverse Characteristics (parameterized on T_J)

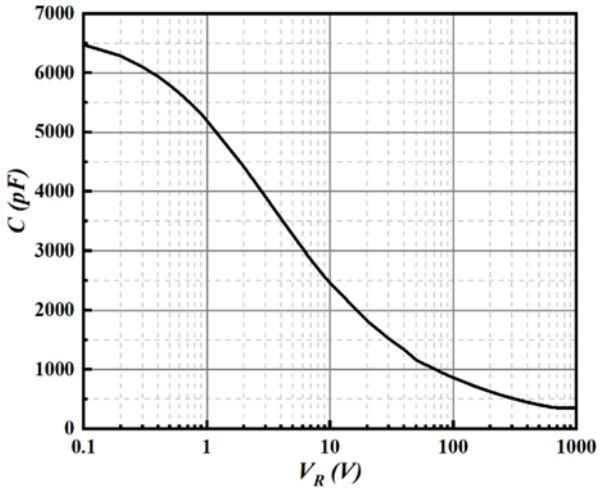


Fig3. Total Capacitance

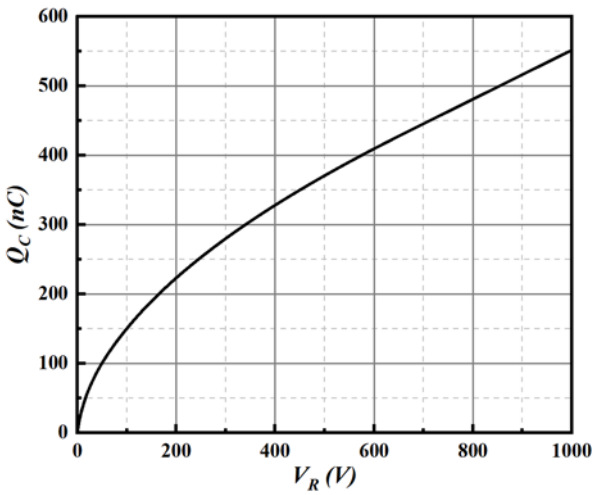


Fig4. Total Capacitive Charge

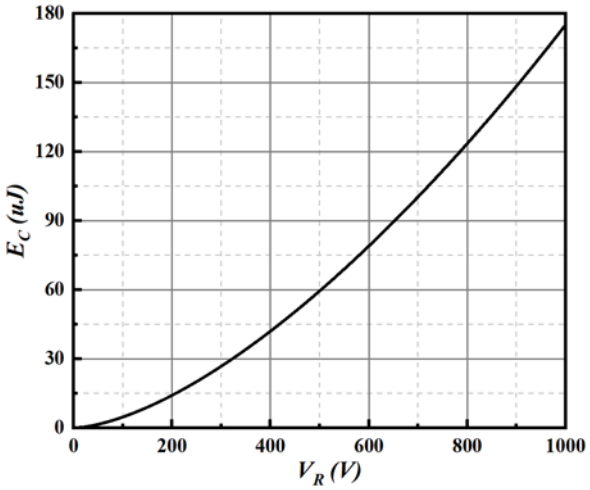


Fig5. Capacitance Stored Energy

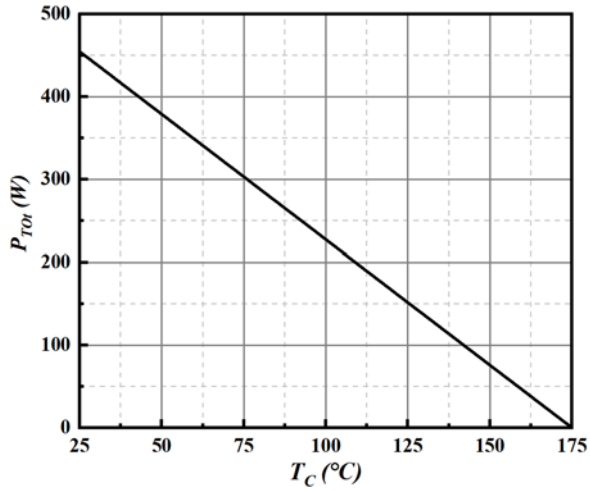


Fig6. Power Derating

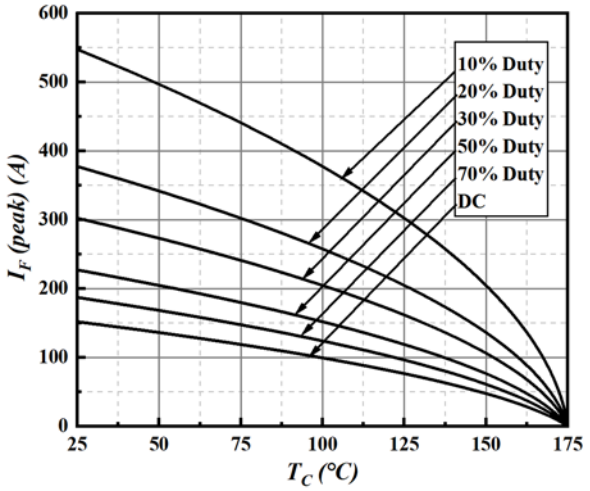


Fig7. Current Derating

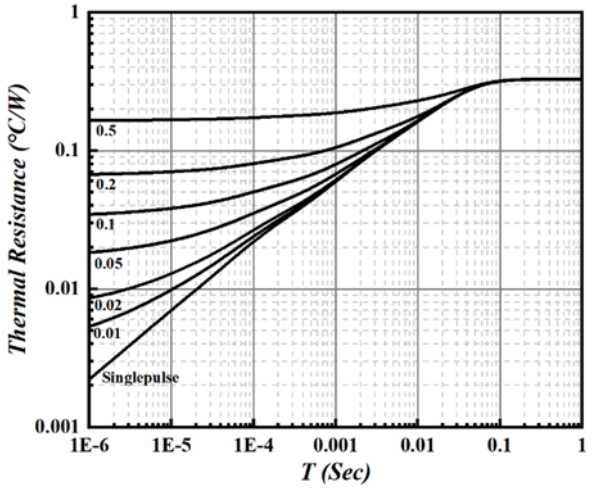
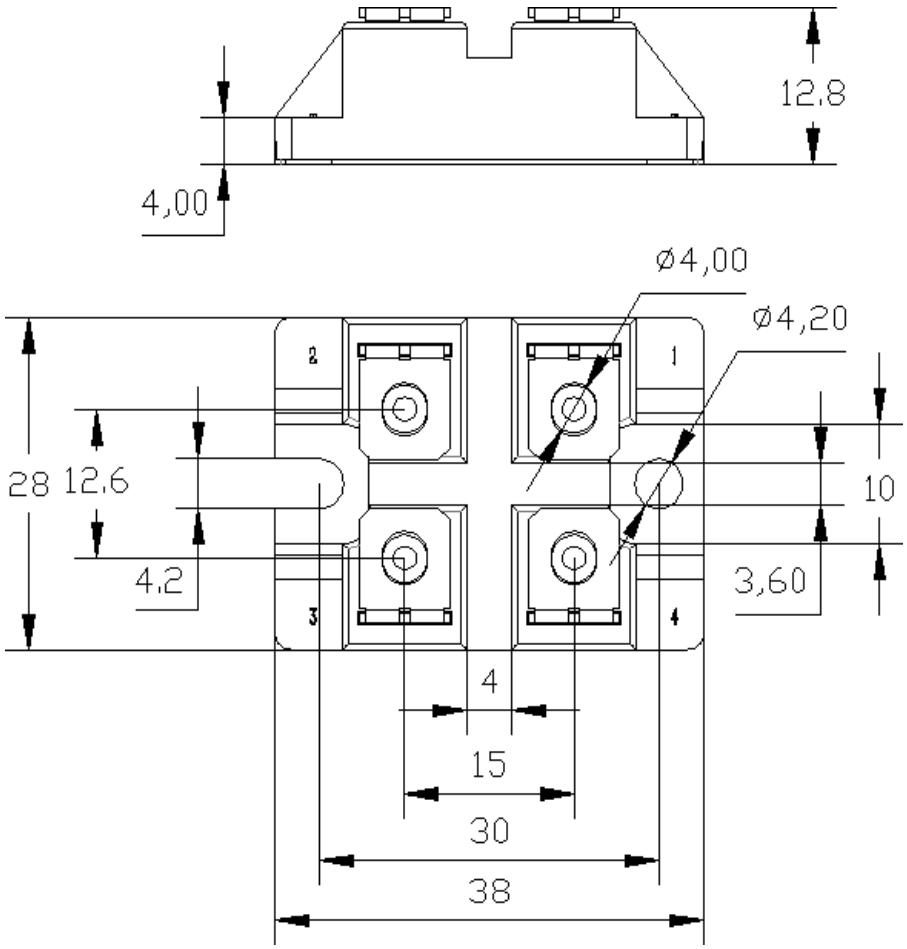


Fig8. Transient Thermal Impedance

Package Outline Information

CASE: FJ



Dimensions in mm

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